Intel i5 660 Microprocessor

32 nm High-k metal gate CMOS process

Package Analysis Preliminary Table of Contents

For comments, questions, or more information about this report, or for any additional technical needs concerning semiconductor technology, please call Sales at Chipworks.

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This **preliminary** table of contents is a direct copy of the Intel 45 nm Xeon processor Package Analysis Report and is intended to provide a general scope of this report.

Final contents will vary based on what is found during reverse engineering.

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